

RELIABILITY REPORT
FOR
MAX9911EWT+
WAFER LEVEL PRODUCTS

March 16, 2012

# **MAXIM INTEGRATED PRODUCTS**

120 SAN GABRIEL DR. SUNNYVALE, CA 94086

Approved by		
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Quality Assurance		
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#### Conclusion

The MAX9911EWT+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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# I. Device Description

#### A. General

The single MAX9910/MAX9911 and dual MAX9912/MAX9913 operational amplifiers (op amps) feature a maximized ratio of gain bandwidth (GBW) to supply current and are ideal for battery-powered applications such as portable instrumentation, portable medical equipment, and wireless handsets. These CMOS op amps feature an ultra-low input-bias current of 1pA, rail-to-rail inputs and outputs, low supply current of 4μA, and operate from a single 1.8V to 5.5V supply. For additional power conservation, the MAX9911/MAX9913 feature a low-power shutdown mode that reduces supply current to 1nA, and puts the amplifiers' outputs in a high-impedance state. These devices are unity-gain stable with a 200kHz GBW product. The MAX9910 is available in a 5-pin SC70 package. The MAX9911 is available in tiny 6-bump WLP and a 6-pin SC70 packages. The MAX9912 is available in an 8-pin SOT23 package, and the MAX9913 is available in a 10-pin μMAX® package. All devices are specified over the -40°C to +85°C extended operating temperature range.



#### II. Manufacturing Information

A. Description/Function: 200kHz, 4µA, Rail-to-Rail I/O Op Amps with Shutdown

B. Process: C6
C. Number of Device Transistors: 201
D. Fabrication Location: Japan
E. Assembly Location: Dallas

F. Date of Initial Production: July 23, 2005

# III. Packaging Information

 A. Package Type:
 6 bmp WLP

 B. Lead Frame:
 N/A

 C. Lead Finish:
 N/A

 D. Die Attach:
 None

E. Bondwire: N/A (N/A mil dia.)
 F. Mold Material: Epoxy with silica filler
 G. Assembly Diagram: #05-9000-4188 / A
 H. Flammability Rating: Class UL94-V0

Classification of Moisture Sensitivity per

JEDEC standard J-STD-020-C

J. Single Layer Theta Ja: N/A
K. Single Layer Theta Jc: N/A
L. Multi Layer Theta Ja: 95°C/W
M. Multi Layer Theta Jc: N/A

### IV. Die Information

A. Dimensions: 37 X 53 mils

B. Passivation: Si3N4/SiO2 (Silicon nitride/ Silicon dioxide)

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C. Interconnect: Al with Ti/TiN Barrier

D. Backside Metallization: None

E. Minimum Metal Width: 0.6 microns (as drawn)F. Minimum Metal Spacing: 0.6 microns (as drawn)

G. Bondpad Dimensions:

H. Isolation Dielectric: SiO<sub>2</sub>I. Die Separation Method: Wafer Saw



#### V. Quality Assurance Information

A. Quality Assurance Contacts: Richard Aburano (Manager, Reliability Engineering)

Don Lipps (Manager, Reliability Engineering)

Bryan Preeshl (Vice President of QA)

B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.

0.1% For all Visual Defects.

C. Observed Outgoing Defect Rate: < 50 ppm
D. Sampling Plan: Mil-Std-105D

# VI. Reliability Evaluation

#### A. Accelerated Life Test

The results of the biased (static) life test are shown in Table 1. Using these results, the Failure Rate ( $\lambda$ ) is calculated as follows:

$$_{\lambda}$$
 =  $\frac{1}{\text{MTTF}}$  =  $\frac{1.83}{192 \times 4340 \times 48 \times 2}$  (Chi square value for MTTF upper limit)

 $_{\lambda}$  = 22.9 x 10<sup>-9</sup>
 $_{\lambda}$  = 22.9 F.I.T. (60% confidence level @ 25°C)

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at http://www.maxim-ic.com/qa/reliability/monitor. Cumulative monitor data for the C6 Process results in a FIT Rate of 0.90 @ 25C and 15.55 @ 55C (0.8 eV, 60% UCL)

# B. E.S.D. and Latch-Up Testing (lot EP8ZAQ001C D/C 1034)

The OY66 die type has been found to have all pins able to withstand a HBM transient pulse of +/-2500V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/-250mA and overvoltage per JEDEC JESD78.



# **Table 1**Reliability Evaluation Test Results

# MAX9911EWT+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (No	ote 1) Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	48	0	EP8ZAQ001C, D/C 1034

Note 1: Life Test Data may represent plastic DIP qualification lots.